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May 2014

FDMC15N06

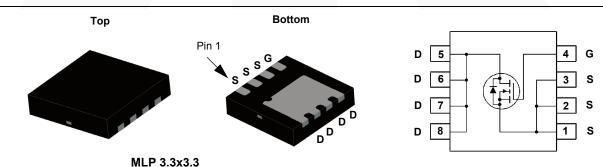
N-Channel UltraFET Power MOSFET 55 V, 15 A, 90 m Ω

Features

- $R_{DS(on)} = 75 \text{ m}\Omega \text{ (Typ.)} @ V_{GS} = 10 \text{ V, } I_D = 15 \text{ A}$
- 100% Avalanche Tested
- · RoHS compliant

Description

These N-Channel power MOSFETs are manufactured using the innovative UltraFET process. This advanced process technology achieves the lowest possible on-resistance per silicon area, resulting in outstanding performance. This device is capable of withstanding high energy in the avalanche mode and the diode exhibits very low reverse recovery time and stored charge. It was designed for use in applications where power efficiency is important, such as switching regulators, switching converters, motor drivers, relay drivers, lowvoltage bus switches, and power management in portable and battery-operated products.



MOSFET Maximum Ratings $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol		Parameter		FDMC15N06	Unit
V _{DSS}	Drain to Source Voltage			55	V
V _{GSS}	Gate to Source Voltage			±20	V
		- Continuous (T _C = 25°C)		15	^
I _D	Drain Current	- Continuous (T _C = 100°C)		9	Α
		- Continuous (T _A = 25°C)	(Note 1a)	2.4	Α
I _{DM}	Drain Current	- Pulsed	(Note 2)	60	Α
E _{AS}	Single Pulsed Avalanch	e Energy	(Note 3)	36	mJ
I _{AR}	Avalanche Current			15	Α
E _{AR}	Repetitive Avalanche E	nergy		3.5	mJ
n	Dower Dissinction	(T _C = 25°C)		35	W
P_{D}	Power Dissipation	$(T_C = 25^{\circ}C)$ $(T_A = 25^{\circ}C)$		2.3	W
T _J , T _{STG}	Operating and Storage	Temperature Range		-55 to +150	°C
TL	Maximum Lead Temper	ature for Soldering, 1/8" from Case for	5 Seconds	300	°C

Thermal Characteristics

Symbol	Parameter	FDMC15N06	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	3.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max. (Note 1a)	53	-0/00

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDMC15N06	15N06	Power 33	Tape and Reel	330 mm	12 mm	3000 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_C = 25^{\circ}C$	55	-	-	V
ΔBV _{DSS} / ΔΤ _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	-	70	-	V/°C
	Zero Gate Voltage Drain Current	V _{DS} = 50 V, V _{GS} = 0 V	-	-	1	
DSS	Zero Gate Voltage Drain Current	$V_{DS} = 45 \text{ V}, T_{C} = 150^{\circ}\text{C}$	-	-	250	μΑ
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	2.0	-	4.0	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 15 A	1	0.075	0.090	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 20 V, I _D = 15 A	1	5	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V - 25 V V - 0 V		-	265	350	pF
C _{oss}	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}$ f = 1 MHz		-	97	130	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 1/1/12		-\	28	42	pF
Q _{g(tot)}	Total Gate Charge at 10V	$V_{DS} = 30 \text{ V}, I_D = 15 \text{ A},$		- \	8.8	11.5	nC
Q _{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	•	- \	1.7	-	nC
Q_{qd}	Gate to Drain "Miller" Charge		(Note 4)	-	3.6	-	nC

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time		-	9.5	29	ns
t _r	Turn-On Rise Time	V _{DD} = 30 V, I _D = 15 A,	-	36.5	83	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} =10 V, R_G =25 Ω	-	22.5	55	ns
t _f	Turn-Off Fall Time	(Note 4)	-	22	54	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current			-	15	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		<i>/</i> -	-	60	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 15 A	-	-	1.25	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 15 A,	-	30	-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$ (Note	5) -	35	/ -	nC

Notes:

^{1.} $R_{\theta,JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta,JC}$ is guaranteed by design while $R_{\theta,CA}$ is determined by the user's board design.



a. 53 °C/W when mounted on a 1 in² pad of 2 oz copper



b.125 °C/W when mounted on a minimum pad of 2 oz copper

- 2: Repetitive rating: pulse-width limited by maximum junction temperature.
- 3: L = 1 mH, I_{AS} = 8.5 A, R_G = 25 Ω , starting T_J = 25°C.
- 4: Essentially independent of operating temperature typical characteristics.
- 5: $I_{SD} \le$ 15 A, di/dt \le 200 A/ μ s, $V_{DD} \le$ 40 V, starting T_J = 25°C.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

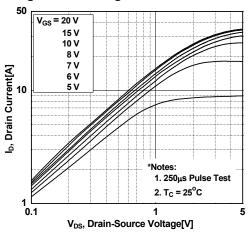


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

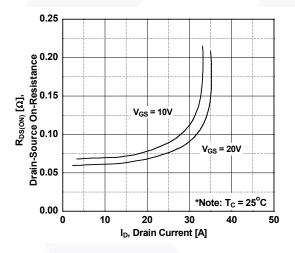


Figure 5. Capacitance Characteristics

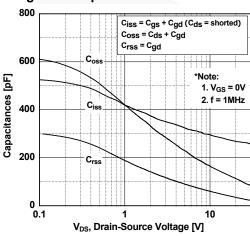


Figure 2. Transfer Characteristics

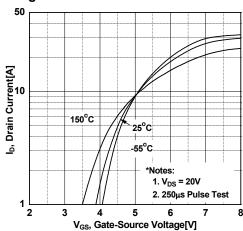


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

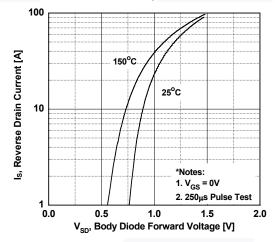
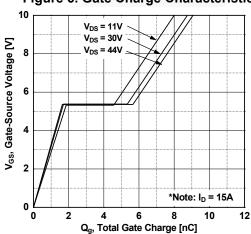


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

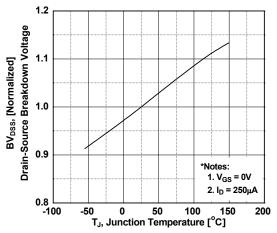


Figure 8. On-Resistance Variation vs. Temperature

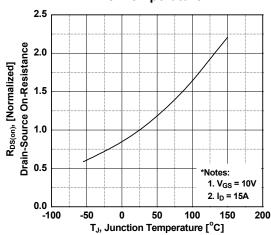


Figure 9. Maximum Safe Operating Area

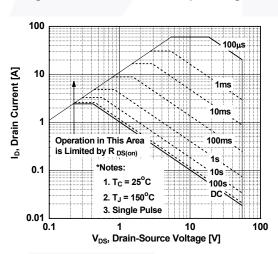


Figure 10. Maximum Drain Current vs. Case Temperature

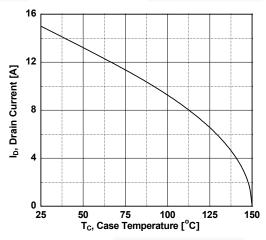
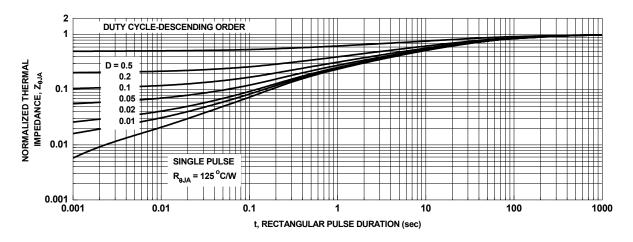


Figure 11. Transient Thermal Response Curve



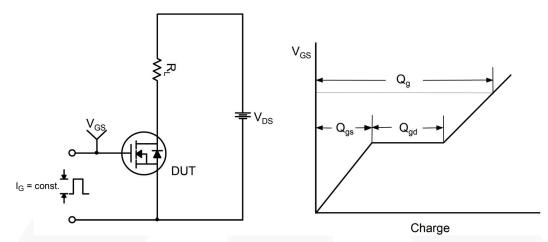


Figure 12. Gate Charge Test Circuit & Waveform

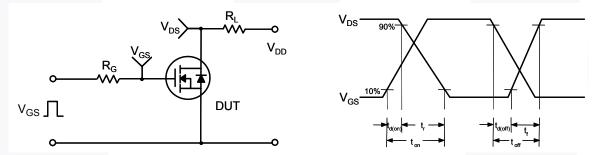


Figure 13. Resistive Switching Test Circuit & Waveforms

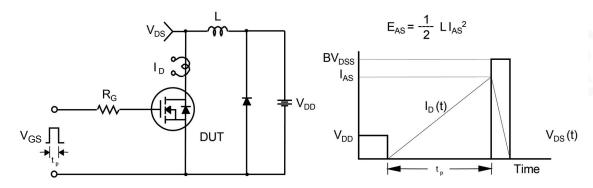


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

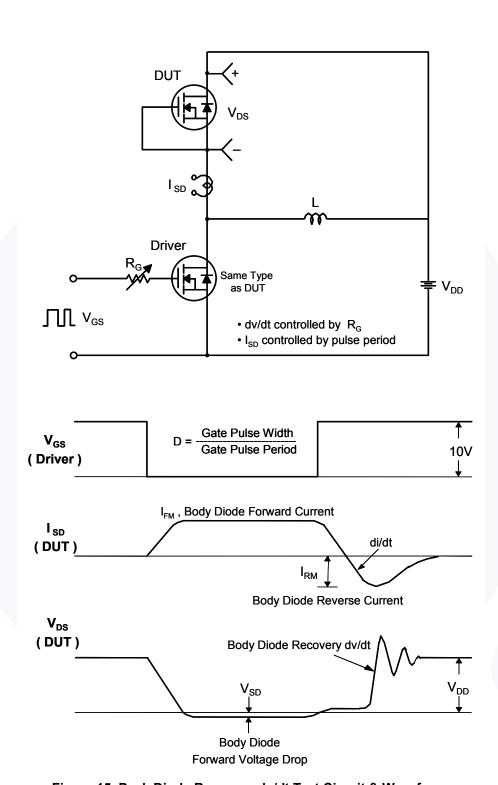


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

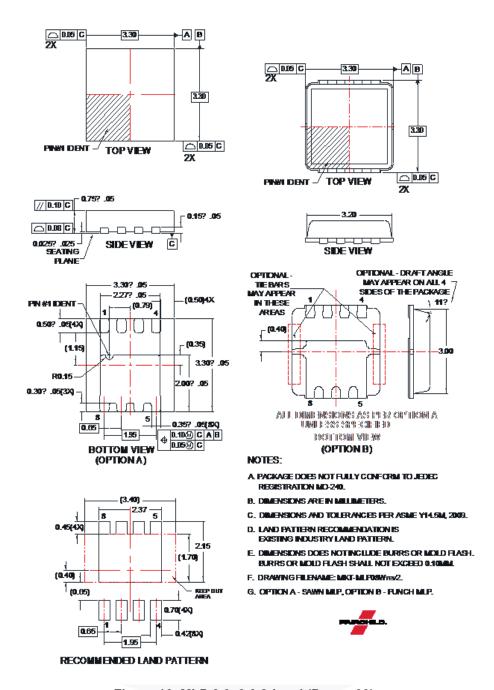


Figure 16. MLP 3.3x3.3 8-Lead (Power 33)

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